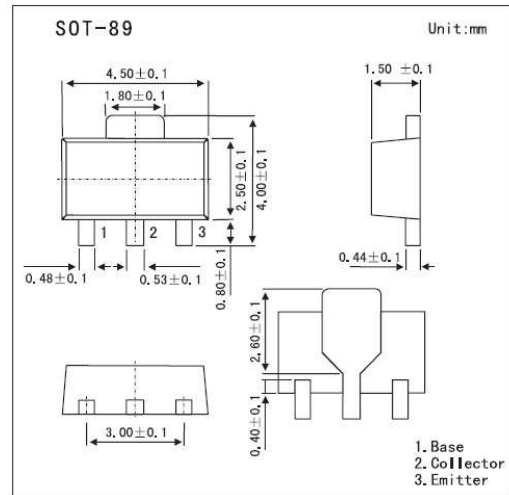


PNP Medium Power Transistor

Features

- High current.
- Three current gain selections.
- 1.2 W total power dissipation.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit	
Collector-base voltage	V _{CB0}	-32	V	
Collector-emitter voltage	V _{CEO}	-20	V	
Emitter-base voltage	V _{EB0}	-5	V	
Collector current	I _C	-1	A	
Peak collector current	I _{CM}	-2	A	
Peak base current	I _{BM}	-200	mA	
Total power dissipation	P _{tot}	*1 and *2	0.5	W
		*1 and *3	0.85	W
		*1 and *4	1.2	W
Storage temperature	T _{stg}	-65 to +150	°C	
Junction temperature	T _j	150	°C	
Operating ambient temperature	R _{amb}	-65 to +150	°C	
Thermal resistance from junction to ambient	R _{th(j-a)}	*1 and *2	250	K/W
		*1 and *3	147	K/W
		*1 and *4	104	K/W
Thermal resistance from junction to solder point	R _{th(j-s)}	20	K/W	

*1.Refer to SOT89 standard mounting conditions.

*2.Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated footprint.

*3.Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 1 cm².

*4.Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm²

■ Electrical Characteristics Ta = 25°C

Parameter		Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current		ICBO	V _{CB} = -25 V, I _E = 0			-100	nA
			V _{CB} = -25 V, I _E = 0; T _j = 25°C			-10	μA
Emitter cutoff current		IEBO	VEB = -5 V, I _C = 0			-100	nA
DC current gain	BC 869	hFE	I _C = -5 mA; V _{CE} = -10 V	50			
			I _C = -500 mA; V _{CE} = -1 V	85		375	
			I _C = -1 A; V _{CE} = -1 V	60			
	BC869-16	hFE	I _C = -500 mA; V _{CE} = -1 V	100		250	
	BC869-25	hFE	I _C = -500 mA; V _{CE} = -1 V	160		375	
Collector-emitter saturation voltage		V _{CE(sat)}	I _C = -1 A; I _B = -100 mA			-500	mV
Base to emitter voltage		V _{BE}	I _C = -5 mA; V _{CE} = -10 V			-700	mV
			I _C = -1 A; V _{CE} = -1 V			-1	V
Collector capacitance		C _C	I _E = I _e = 0; V _{CB} = -10 V; f = 1 MHz		28		pF
Transition frequency		f _T	I _C = -50 mA; V _{CE} = -5 V; f = 100 MHz	40	140		MHz

■ hFE Classification

TYPE	BC869	BC869-16	BC869-25
Marking	CEC	CGC	CHC

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